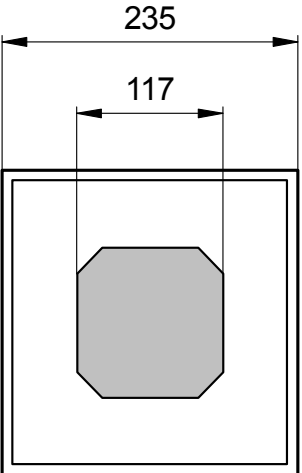


Radiation	Type	Technology	Electrodes
Green	Standard	GaP/GaP	P (anode) up

	typ. dimensions (μm)	
	<u>typ. thickness</u> 270 (±20) μm <u>cathode</u> gold alloy, 1.5 μm <u>anode</u> gold alloy, 0.5 μm structured, 25% covered	

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		2.1	2.4	V
Reverse voltage	I _R = 10 μA	V _R	5			V
Radiant power ¹	I _F = 20 mA	Φ _e	28	32		μW
Radiant power ²	I _F = 20 mA	Φ _e		60		μW
Luminous intensity ¹	I _F = 20 mA	I _V	1	1.2		mcd
Luminous intensity ²	I _F = 20 mA	I _V		2.4		mcd
Peak wavelength	I _F = 20 mA	λ _P	550	560	570	nm
Dominant wavelength	I _F = 20 mA	λ _D		563		nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		24		nm

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	I _V (typ) [mcd]	V _F (typ) [V]	Quantity
ELC-560-10				

Packing: Chips on adhesive film with wire-bond side on top

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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